

CHAPTER - VDIELECTRIC PERMITTIVITY5.1 INTRODUCTION

The most common and significant non-linear property of ferroelectric materials is the dielectric constant or dielectric permittivity (ϵ). Since the permittivity (ϵ) expresses the behaviour of polarization, it is clearly close to the heart of ferroelectricity. The dielectric constant (ϵ) is defined as the ratio of the capacitance of a capacitor filled with the dielectric material to that of empty capacitor and hence a dimensionless parameter. It is a rarely constant, but changes with applied field, stress, temperature and other parameters. It is well known that the spontaneous polarization of the material decreases with temperature and finally reduces to zero at Curie temperature increasing dielectric constant to a peak value. Polar dielectric materials characteristically have much higher values of ϵ (in the range 100-10000) than non-polar dielectric materials (ϵ in the range 1-10). The most polar materials show a large increase in ϵ at a temperature in the region of a crystalline phase transition temperature. This anomaly of ϵ , of the ferroelectric material at the Curie-weiss temperature shows maximum value of ϵ and material goes from polar phase (ferroelectric state) to non-polar phase (paraelectric state). In the paraelectric phase ϵ obeys the expression,

$$\epsilon = \frac{C}{T-T_0} \quad \dots 5.1$$

where C is Curie constant, T_0 is Curie-Weiss temperature. Equation 5.1 is the electrical equivalent of the Curie-Weiss behaviour observed in ferromagnetic materials. Similarly, an important dielectric property of the polar materials, is a dissipation factor i.e. $\tan \delta$ which is a mere ratio of imaginary part to real part of ϵ . Most polar dielectrics are very good insulators and hence have a low value of $\tan \delta$. $\tan \delta$ like ϵ , also shows anomalous behaviour at T_c .

The most detailed study of titania ceramics on high dielectric constant was carried out by Von-Hippel et al (1946). Smolenski (1950) reported peakvalue of ϵ of SrTiO_3 ceramic in the temperature range $20-30^\circ\text{k}$. The dielectric constant of PbTiO_3 ceramic was measured as a function of temperature by Shirane et al (1951). The dielectric constant of lead-strontium titanate series in the temperature range from -150°c to 300°c was measured by Nomura et al (1955). Akao et al (1955) reported that the temperature dependence of the real part of ϵ of Rochelle salt for different values of the measuring frequency. Marutake (1956) computed high values of dielectric constant in BaTiO_3 . Granicher's (1958) dielectric measurements on single crystals of SrTiO_3 revealed that the Curie-Weiss law is obeyed at 95°k . Few investigators except Rupprecht et al (1961) and Diamond (1961) observed an explicit relationship between ϵ and external applied electric field. Theory of Rupprecht is valid for small fields only and that of Diamond's theory is applicable to polycrystalline materials which are more lossy. Schlosser et al (1961) investigated that the capacitance and dielectric loss of crystal

wafers depend up on their thickness. Dielectric constant measurements of ferroelectric NaNbO_3 crystal were made by Shoichiro Nomura (1961). Stern and Lurio (1961) used the phenomenological theory of Devonshire (1945, 1954) in which they determined the change in dielectric constant with applied electric field. The effect of different factors on the dielectric constant of SrTiO_3 was studied by Hegenberth (1964) and Samara et al (1965). Measurements of the dependence of dielectric constant on grain size of BaTiO_3 , as a function of temperature were described by Miller (1967). The variation of the dielectric constant and loss tangent at 1MHz as a function of d.c. voltage in (Ba-Sr) TiO_3 and (Pb-Sr) TiO_3 system was determined by Griffiths (1970). Coufora et al (1972) were studied dielectric properties of $(\text{Ba}_{1-x}\text{-Sr}_x)\text{TiO}_3$ single crystal. The dielectric behaviour of different particle size powders of barium titanate, potassium ferrocyanide trihydrate and ammonium sulphate was studied by Mansingh et al (1974). The dielectric properties of $(\text{Sr}_{1-x}\text{-Pb}_x)\text{TiO}_3$ solid solution at low temperatures and high pressures were studied by Martin et al (1976). The results of variation of overall dielectric constant of BaTiO_3 single crystal with applied a.c. electric field and crystal temperature were reported by Deshpande et al (1977). Optical and dielectric studies on SrTiO_3 & KTaO_3 were carried out by Fujii et al (1977). Glass et al (1978) studied the dielectric constant variation of calcium orthovanadate and observed peak value of dielectric constant at the Curie temperature. Ismailzade et al (1980) were investigated dielectric measurements of polycrystalline samples of the rare earth arsenates RAsO_4 (R=Pr, Nd, Eu, Gd, Tb, Dy, Er or Yo) at

1 KHz frequency. V.K. Yanovski (1980) was studied temperature dependence of ϵ of KNbO_3 crystal. Further, Ismailzade et al (1981) discovered new oxide ferroelectrics RVO_4 ($\text{R}=\text{Nd, Eu, Gd, Tb, Dy, Ho, Er, Yb, Lu}$ and Sc) and from the variation of ϵ with temperature observed maximum value of ϵ at ferroelectric Curie temperatures of these materials. Several physical properties of lead titanate such as measurement of DTA curve, dielectric constant, Raman scattering and microscopic observations have been made by Takashige et al (1981). The dielectric constant ϵ_c of poled tetragonal BaTiO_3 was measured in frequency range 0.1 to 6 GHz by Clemens et al (1981). Mathur et al (1981) were reported dielectric constant of mixed crystals of TGS and TGSB. Yamashita et al (1982) were measured dielectric constant of ceramic BaTiO_3 under high d.c. biasing field of 5 to 20 KV/cm. R.Chaves et al (1982) were studied dielectric constant of $\text{SbSe}_x\text{S}_{1-x}\text{I}$ in weak fields at 1KHz. Dielectric and pyroelectric properties of sintered discs of NaVO_3 were reported by Khan et al (1983) and observed anomalies in dielectric constant around 375-390°C. They also showed that the anomalous property of dielectric constant is independent of the electrode material used and poling of the sample. The rate of surface layers in dielectric measurements in oxide perovskites such as SrTiO_3 and BaTiO_3 was discussed by Stumpe et al (1984). Molokhia et al (1984) were investigated the dielectric constant of BaTiO_3 doped with Yb_2O_3 at different concentrations at different temperatures. Similarly, Issa et al (1984) studied dielectric properties of BaTiO_3 doped with Gd_2O_3 having different concentrations. S.H.Chavan and P.G.Kulkarni (1985) studied dielectric and hysteresis properties of ferroelectric solid solutions of barium-strontium and

barium-calcium titanate. Jamadar et al (1986) investigated dielectric constants of lead-barium and lead-strontium titanate. Patil et al (1989) investigated dielectric properties of KVO_3 , $LiVO_3$ and their solid solutions. Recently, Patil et al (1990) have studied dielectric properties of KVO_3 doped with Nd_2O_3 and Kashid et al (1990) also have studied temperature dependence of dielectric constant of KVO_3 and $LiVO_3$ doped with different concentrations of Gd_2O_3 .

In this investigation, the temperature dependence of dielectric constant of KVO_3 doped with Er_2O_3 for various concentrations are studied.

5.2 EXPERIMENTAL

The dielectric permittivity (ϵ) of the ferroelectric material is generally measured by using method based on the principle of comparison of two capacities. The ratio $\frac{C_1}{C_2} = \epsilon$, is called dielectric constant, where C_1 is capacity of capacitor filled with the substance and C_2 is the capacity of the empty capacitor containing air. The LC resonant circuit is used for the determination of capacitance as shown in Fig. 5.1. The circuit consists of inductance L, C_s the calibrated variable capacitor and C capacitor in which the specimen may be placed. The experimental arrangement used for the measurement of dielectric constant at various temperatures is shown in Fig. 5.2, which consists of an electrically heated furnace with a temperature controller arrangement and the digital capacitance bridge (LCR METER VLCR 7). The

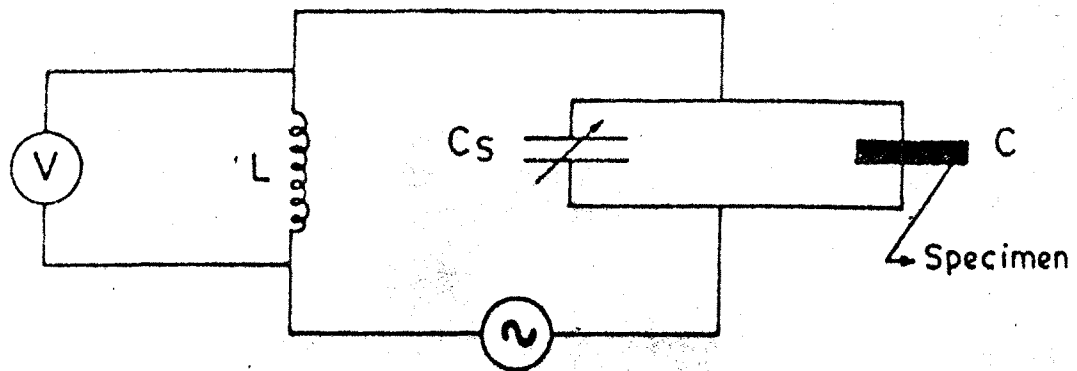


Fig. 51— SCHEMATIC DIAGRAM OF APPARATUS FOR THE MEASUREMENT OF DIELECTRIC CONSTANT.

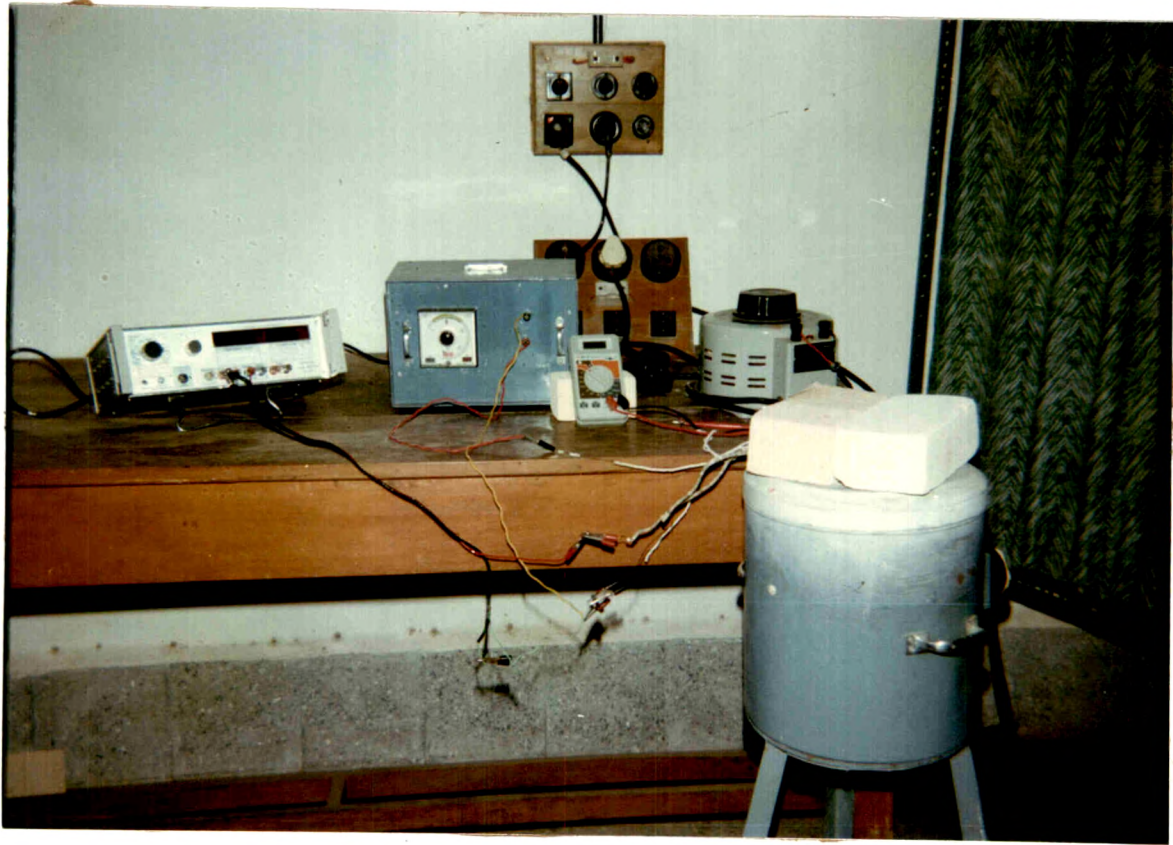


Fig. 5.2 : Experimental set-up for measurement of dielectric permittivity.



pellets of the samples of undoped KVO_3 and doped KVO_3 with Er_2O_3 , having thickness about 1 mm were sintered at 750°C and then faces of pellets were coated with thin layer of silver paste to achieve good electrical contact with electrodes in a sample holder. From the capacitance measurement data and capacitance of air in the empty capacitor dielectric constants at different temperatures were calculated by using above mentioned method. The variation of dielectric constant with temperature of undoped and doped KVO_3 with different concentrations of Er_2O_3 (0.025 to 3 mol %) is shown in Fig. 5.3.

5.3 RESULTS AND DISCUSSION

Fig. 5.3 reveals us that the dielectric constant of undoped and doped KVO_3 with Er_2O_3 having different concentrations (0.025 mol % to 3 mol %) is temperature dependent. It is also seen that the maximum(peak) values of dielectric constant of different samples are observed at different temperatures indicating their Curie temperatures. The Curie temperatures of these samples are quite in good agreement with the Curie temperatures confirmed by dielectric hysteresis study as well as pyroelectric measurement technique. Fig. 5.3 shows the decrease in Curie temperature of KVO_3 as dopant (Er_2O_3) concentration in it increases. The peak values of ϵ , Curie temperature and density of the samples are summarized in Table 5.1.

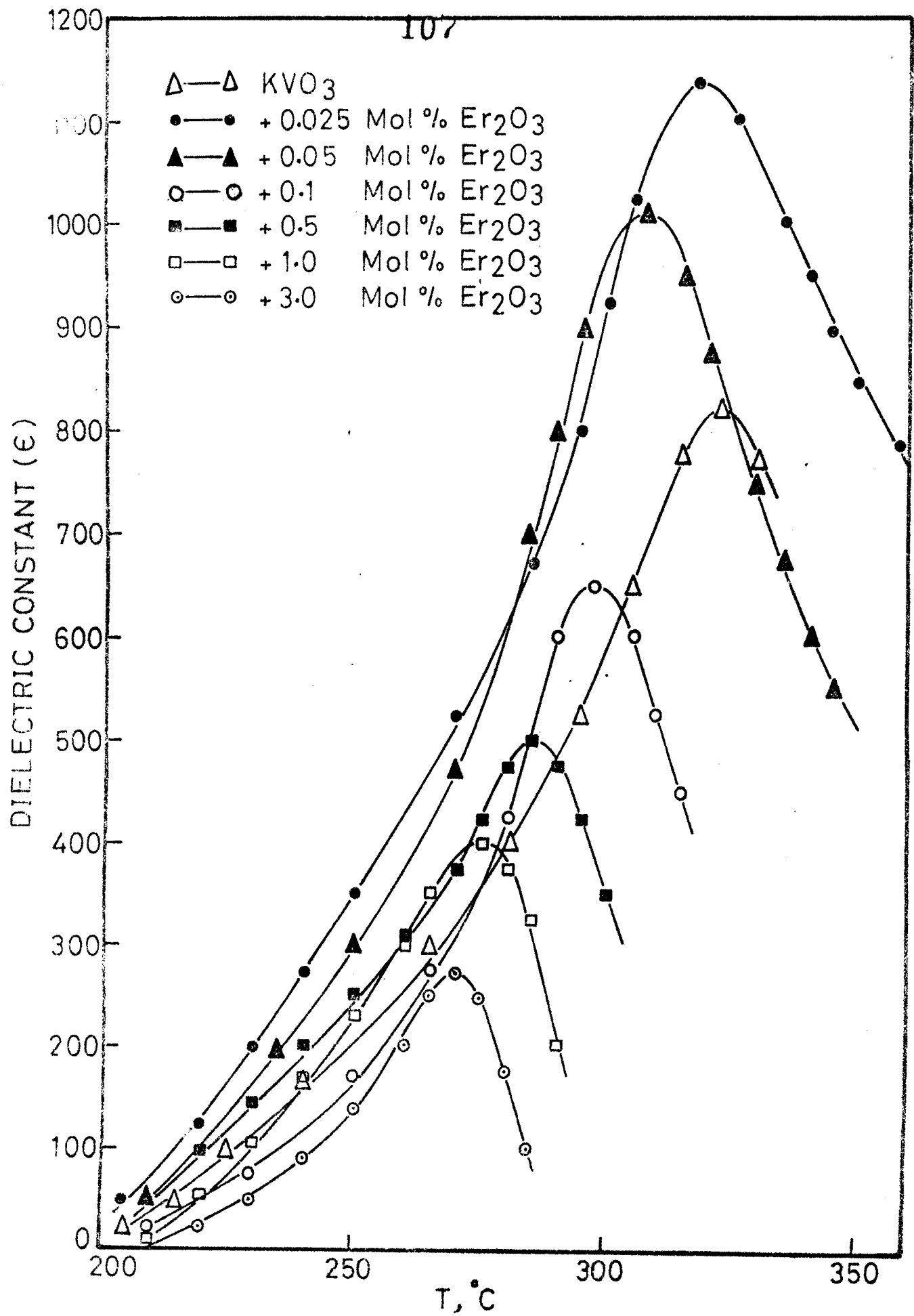


Fig.5.3 VARIATION OF DIELECTRIC CONSTANT WITH TEMPERATURE FOR UNDOPED AND DOPED KVO_3 WITH Er_2O_3 .

TABLE 5.1
 ϵ_{\max} CURIE TEMPERATURE AND DENSITY OF SAMPLES

| Er ₂ O ₃ content Mol % | ϵ_{\max} | Curie Temp. °C | Density gm/cc |
|---|-------------------|-------------------|------------------|
| 0.000 | 820 | 322.5 | 2.50 |
| 0.025 | 1140 | 317.5 | 2.61 |
| 0.050 | 1010 | 307.5 | 2.58 |
| 0.100 | 650 | 297.5 | 2.51 |
| 0.500 | 500 | 285.0 | 2.47 |
| 1.000 | 400 | 275.5 | 2.43 |
| 3.000 | 275 | 260.0 | 2.40 |

Table 5.1 shows ϵ_{\max} is higher for KVO₃ samples containing 0.025, 0.05 and 0.1 mol % Er₂O₃ and it is smaller for samples containing 0.5, 1 and 3 mol % Er₂O₃, as compared to ϵ_{\max} for undoped KVO₃. The dielectric constant ϵ_{\max} is highest for 0.025 mol % Er₂O₃ in KVO₃. This table also indicates that ϵ_{\max} is a function of density of the sample showing ϵ_{\max} is higher for higher density of KVO₃ doped with 0.025 mol % Er₂O₃. This indicates that dielectric saturation state is observed for 0.025 mol % doping of Er₂O₃ in KVO₃. Fig 5.3 also shows broad peak nature for all the samples indicating diffuse phase transition at Curie temperature.

From the present investigation following conclusions could be drawn.

CONCLUSIONS

1. Dielectric constant varies with temperature for undoped and Er_2O_3 doped KVO_3 samples. i.e. it increases with temperature showing a peak value at the Curie point and decreases with further rise in temperature, obeying the Curie-Weiss law.
2. Peak value of ϵ represents Curie temperature of that sample.
3. ϵ_{max} is different for different samples.
4. Curie temperatures of all the samples are matching with those confirmed by dielectric hysteresis and pyroelectric measurement experiments.
5. ϵ_{max} is maximum for the KVO_3 containing 0.025 mol % of Er_2O_3 indicating the dielectric saturation state of ferroelectric ceramic.

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